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New TriQuint Base Station RFICs Integrate Unique Protections for Data-Intensive Mobile Device Networks

Meet TriQuint's Experts at IMS 2011 and Discover New Ways to Lower Power Consumption and Prevent Network System ESD, RF Over-Drive & DC Over-Voltage Failures

BALTIMORE & HILLSBORO, Ore.--(BUSINESS WIRE)-- TriQuint Semiconductor (NASDAQ:TQNT), a leading RF solutions supplier and technology innovator, has released the first members in a new family of integrated RF products that lower power consumption while protecting mobile networks from disruption and service failures. TriQuint's newest base transceiver station (BTS) network devices join 12 other new power and filter infrastructure solutions introduced in the first half of 2011.

"We listened to our customers in developing these products," said Vice President Brian P. Balut. "Consumer demand for smartphones and tablets means more bandwidth through the network. That leads to the requirement for greater linearity in the RF chain. At the same time, our customers want to minimize power consumption, and they want devices that withstand spikes and other stresses that may occur in the field. These two new products uniquely address all these needs."

TriQuint is focused on bringing performance innovation to essential building blocks in the global network. This network is fraught with demand, and it's not going to let up; by 2015, the amount of mobile data traffic contributed by tablets alone is expected to equal that of mobile data traffic from all devices combined in 2010.*

TriQuint's new base station devices, starting with the 0.25 Watt TQP7M9101, provides high gain and linearity with very low current consumption—just 88 mA (milliamps) in a typical 5 Volt design. The 0.5 Watt TQP7M9102 is also now available; it provides highly-linear performance, low current consumption and greater gain.

Setting these amplifiers apart from others now available is TriQuint's patent-pending integrated protection features that include means to guard against ESD and DC over-voltage electrical spikes. TriQuint also integrates RF over-drive protection that reduces the chance of damage from high signal levels often seen in systems employing digital pre-distortion linearization techniques commonly utilized to meet 3G/4G BTS system requirements. Unlike other linear driver amplifiers available today, TriQuint's TQP7M9101 also integrates matching circuits that eliminate the need externally. These integration benefits reduce the overall BOM and provide easier-to-use solutions that are especially important when fast time-to-market is a key manufacturer strategy.

"TriQuint regularly releases new amplifier and linear gain blocks that offer useful improvements. They appreciate that design requirements change all the time," said Alexander Kopp, RF designer, Andrew Wireless Systems / CommScope, Buchdorf, Germany. "A more linear RF signal is very important, and with very low current drain, we can reduce a system's thermal dissipation. The TriQuint team has offered us great support."

TriQuint's two new amplifiers are ideal for 3G/4G wireless infrastructure applications including base transceiver stations, repeaters, boosters, tower-mounted amplifiers (TMAs), remote radio heads, defense/aerospace and other wireless systems requiring high linearity and gain with low power consumption.

TriQuint's base station, microwave and defense/aerospace innovations will be displayed at the IEEE IMS / MTT-S Conference and Exhibition (June 5-10, Baltimore, Maryland.) Visit TriQuint at Booth #2218, or request a meeting with our experts at: info-networks@tqs.com. For information about future product releases and to subscribe to our newsletter, visit www.triquint.com/rf.

**Source: 2011 Cisco Visual Networking Index*

Technical Details

TQP7M9101	0.25W high-linearity amplifier. Performance at 2.1 GHz: 17.5 dB gain, 40 dBm OIP3 & 24.8 dBm P1dB while consuming only 88 mA current from a 5V supply. Integrated RF over-drive, DC over-voltage and Class 2 (2000V) HBM ESD protection.
TQP7M9102	0.5W high-linearity amplifier. Performance at 2.1 GHz: 17.8 dB gain, 43.5 dBm OIP3 & 27.5 dBm P1dB while consuming only 137 mA current from a 5V supply. Integrated RF over-drive, DC over-voltage and Class 2 (2000V) HBM ESD protection.

FORWARD LOOKING STATEMENTS

This TriQuint Semiconductor, Inc. (NASDAQ:**TQNT**) press release contains forward-looking statements made pursuant to the Safe Harbor provisions of the Private Securities Litigation Reform Act of 1995. Readers are cautioned that forward-looking statements involve risks and uncertainties. The cautionary statements made in this press release should be read as being applicable to all related statements wherever they appear. Statements containing such words as ‘leading', ‘exceptional', ‘high efficiency', ‘key role', ‘leading supplier', or similar terms are considered to contain uncertainty and are forward-looking statements. A number of factors affect TriQuint's operating results and could cause its actual future results to differ materially from any results indicated in this press release or in any other forward-looking statements made by, or on behalf of, TriQuint including, but not limited to: those associated with the unpredictability and volatility of customer acceptance of and demand for our products and technologies, the ability of our production facilities and those of our vendors to meet demand, the ability of our production facilities and those of our vendors to produce products with yields sufficient to maintain profitability, as well as the other "Risk Factors" set forth in TriQuint's most recent 10-Q report filed with the Securities and Exchange Commission. This and other reports can be found on the SEC web site, www.sec.gov. A reader of this release should understand that these and other risks could cause actual results to differ materially from expectations expressed / implied in forward-looking statements.

FACTS ABOUT TRIQUINT

Founded in 1985, TriQuint Semiconductor (NASDAQ:TQNT) is a leading global provider of innovative RF solutions and foundry services for the world's top communications, defense and aerospace companies. People and organizations around the world need real-time, all-the-time connections; TriQuint products help reduce the cost and increase the performance of connected mobile devices and the networks that deliver critical voice, data and video communications. With the industry's broadest technology portfolio, recognized R&D leadership, and expertise in high-volume manufacturing, TriQuint creates standard and custom products using gallium arsenide (GaAs), gallium nitride (GaN), surface acoustic wave (SAW) and bulk acoustic wave (BAW) technologies. The company has ISO9001-certified manufacturing facilities in the U.S., production in Costa Rica, and design centers in North America and Germany. For more information, visit www.triquint.com.

TriQuint: Connecting the Digital World to the Global Network®

Photos/Multimedia Gallery Available: http://www.businesswire.com/cgi-bin/mmg.cgi?eid=6749044&lang=en

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